

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
27 December 2002 (27.12.2002)

PCT

(10) International Publication Number
WO 02/103375 A2

(51) International Patent Classification⁷: **G01R 21/00**

(21) International Application Number: PCT/US02/18963

(22) International Filing Date: 13 June 2002 (13.06.2002)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
09/882,443 14 June 2001 (14.06.2001) US

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(81) Designated States (*national*): AE, AG, AL, AM, AT, AU,
AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU,
CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH,
GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC,
LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW,
MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SD, SE, SG,
SI, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VN,
YU, ZA, ZM, ZW.

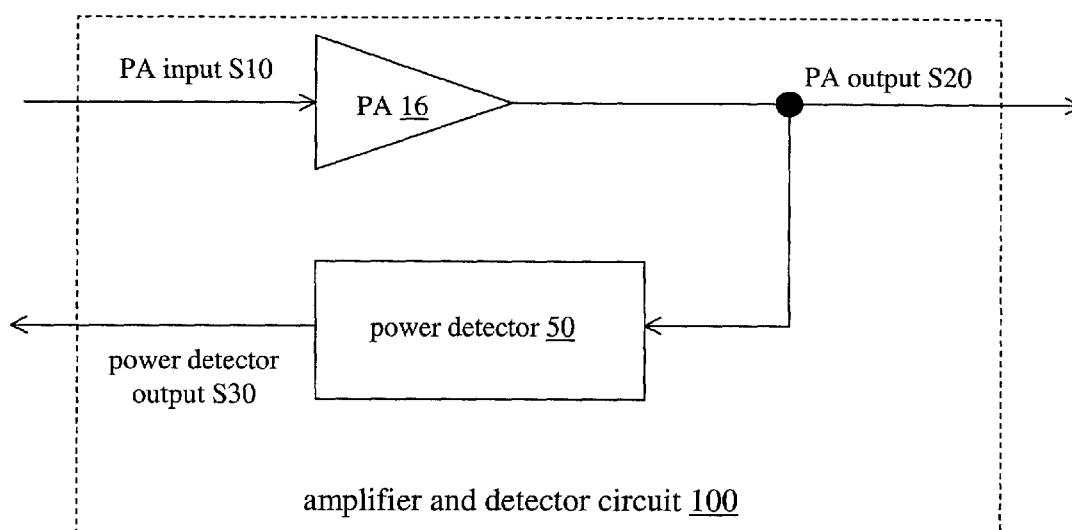
(84) Designated States (*regional*): ARIPO patent (GH, GM,
KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW),
Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR,
GB, GR, IE, IT, LU, MC, NL, PT, SE, TR), OAPI patent
(BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR,
NE, SN, TD, TG).

Published:

— *without international search report and to be republished
upon receipt of that report*

*For two-letter codes and other abbreviations, refer to the "Guid-
ance Notes on Codes and Abbreviations" appearing at the begin-
ning of each regular issue of the PCT Gazette.*

(54) Title: INTEGRATED POWER DETECTOR WITH TEMPERATURE COMPENSATION



(57) Abstract: A power detector (50) detects a power level of an amplified signal (S20) produced by a power amplifier (16) on the same integrated circuit (100). The power detector compensates for an effect of temperature variations on the magnitude of the detected power level.



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